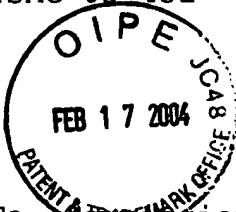


TSMC-03-431



February 9, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/718,881 11/21/03 |

Yi-Lung Cheng et al.

A METHOD OF FORMING A BORDERLESS
CONTACT OPENING FEATURING A COMPOSITE
TRI-LAYER ETCH STOP MATERIAL

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on February , 2004.

Stephen B. Ackerman, Reg.# 37761

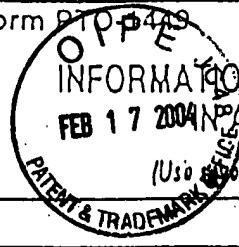
Signature/Date Stephen B. Ackerman 2/12/04

The following four U.S. Patents describe methods of forming self-aligned contact and via openings using underlying etch stop layers:

- 1) U.S. Patent 5,972,722 to Visokay et al., "Adhesion Promoting Sacrificial Etch Stop Layer in Advanced Capacitor Structures."
- 2) U.S. Patent 5,596,230 to Hong, "Interconnection with Self-aligned Via Plug."
- 3) U.S. Patent 5,731,242 to Parat et al., "Self-aligned Contact Process in Semiconductor Fabrication."
- 4) U.S. Patent 6,080,674 to Wu et al., "Method for Forming Via Holes."

Sincerely,


Stephen B. Ackerman,
Reg. No. 37761



Block Lof

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.